

## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	30
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V	0.003
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.004
$I_D$ (A)	120
Configuration	Single

### FEATURES

- TrenchFET® Power MOSFET
- 100 %  $R_g$  and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



RoHS  
COMPLIANT

### APPLICATIONS

- OR-ing
- Server
- DC/DC

TO-220AB



G D S  
Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	$T_C = 25$ °C	120
		$T_C = 70$ °C	60 <sup>e</sup>
		$T_A = 25$ °C	28.8 <sup>b, c</sup>
		$T_A = 70$ °C	19 <sup>b, c</sup>
Pulsed Drain Current	$I_{DM}$	380	A
Avalanche Current Pulse	$I_{AS}$	36	
Single Pulse Avalanche Energy			
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C	90 <sup>a, e</sup>
		$T_A = 25$ °C	3.13 <sup>b, c</sup>
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	250 <sup>a</sup>
		$T_C = 70$ °C	175
		$T_A = 25$ °C	3.75 <sup>b, c</sup>
		$T_A = 70$ °C	2.63 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	32	40	°C/W	
Maximum Junction-to-Case	$R_{thJC}$	0.5	0.6		

Notes:

a. Based on  $T_C = 25$  °C.

b. Surface mounted on 1" x 1" FR4 board.

c.  $t = 10$  sec.

d. Maximum under steady state conditions is 90 °C/W.

e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	90			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 28.8\text{ A}$		0.003		$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 27\text{ A}$		0.004		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 28.8\text{ A}$		160		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		3100		pF
Output Capacitance	$C_{oss}$			725		
Reverse Transfer Capacitance	$C_{rss}$			370		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 28.8\text{ A}$		171	257	nC
				81.5	123	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 28.8\text{ A}$		34		
Gate-Drain Charge	$Q_{gd}$			29		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.4	2.1	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.625\text{ }\Omega$ $I_D \cong 24\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		18	27	ns
Rise Time	$t_r$			11	17	
Turn-Off Delay Time	$t_{d(off)}$			70	105	
Fall Time	$t_f$			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.67\text{ }\Omega$ $I_D \cong 22.5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		55	83	
Rise Time	$t_r$			180	270	
Turn-Off Delay Time	$t_{d(off)}$			55	83	
Fall Time	$t_f$			12	18	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			90	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				90	
Body Diode Voltage	$V_{SD}$	$I_S = 22\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		52	78	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			70.2	105	nC
Reverse Recovery Fall Time	$t_a$			27		ns
Reverse Recovery Rise Time	$t_b$			25		

Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



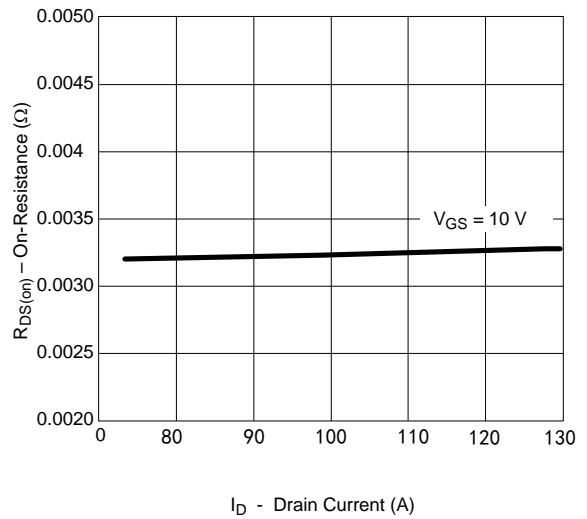
**Output Characteristics**



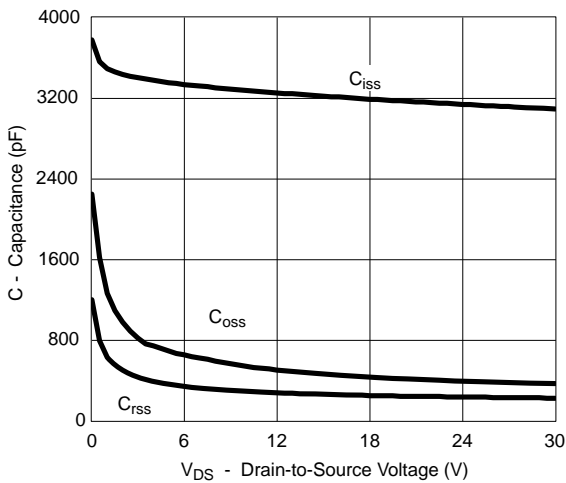
**Transfer Characteristics**



**Transconductance**



**$R_{DS(on)}$  vs. Drain Current**



**Capacitance**



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**On-Resistance vs. Junction Temperature**



**Forward Diode Voltage vs. Temperature**



**$R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature**

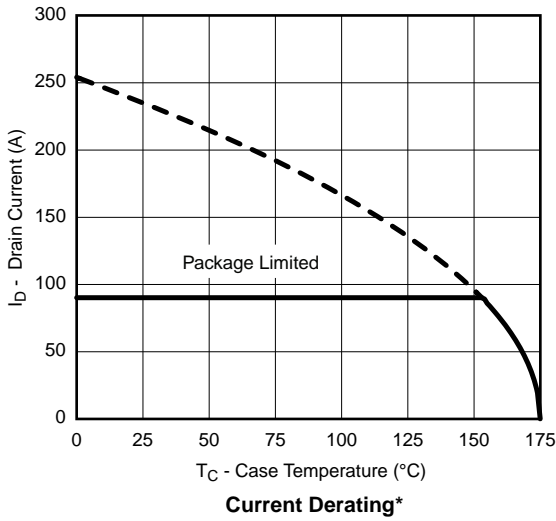


**Threshold Voltage**



**Safe Operating Area, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



\*The power dissipation P<sub>D</sub> is based on T<sub>J(max)</sub> = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



### TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

**Notes**

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM

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